# **Amplifier Transistors**

## **PNP Silicon**

#### **Features**

• Pb-Free Packages are Available\*

#### **MAXIMUM RATINGS**

Rating	Sym	bol Value	Unit
B	C556 C557 C558	-65 -45 -30	Vdc
В	C556 C557 C558	-80 -50 -30	Vdc
Emitter - Base Voltage	V <sub>EE</sub>	<sub>3O</sub> –5.0	Vdc
Collector Current – Continuous – Peak	I <sub>C</sub>		mAdc
Base Current – Peak	IBN	<sub>M</sub> –200	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	C P <sub>C</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	C P <sub>C</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	Т <sub>Ј</sub> , Т	-55 to +150	°C

#### THERMAL CHARACTERISTICS

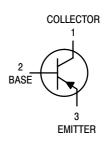
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

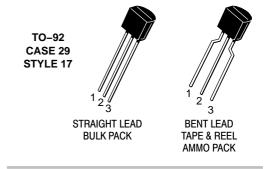
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



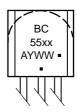
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#### **MARKING DIAGRAM**



xx = 6B, 7A, 7B, 7C, or 8B A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = -2.0 mAdc, I <sub>B</sub> = 0)	BC556 BC557 BC558	V <sub>(BR)CEO</sub>	-65 -45 -30	- - -	- - -	V
Collector – Base Breakdown Voltage (I <sub>C</sub> = –100 μAdc)	BC556 BC557 BC558	V <sub>(BR)</sub> CBO	-80 -50 -30	- - -	- - -	V
Emitter – Base Breakdown Voltage ( $I_E = -100 \mu Adc, I_C = 0$ )	BC556 BC557 BC558	$V_{(BR)EBO}$	-5.0 -5.0 -5.0	- - -	- - -	V
Collector–Emitter Leakage Current (V <sub>CES</sub> = -40 V) (V <sub>CES</sub> = -20 V) (V <sub>CES</sub> = -20 V, T <sub>A</sub> = 125°C)	BC556 BC557 BC558 BC556	I <sub>CES</sub>	- - - -	-2.0 -2.0 -2.0	-100 -100 -100 -4.0	nA μA
	BC557 BC558		_	_	-4.0 -4.0	
ON CHARACTERISTICS	<u>.</u>		•			
DC Current Gain $(I_C = -10 \ \mu Adc, \ V_{CE} = -5.0 \ V)$ $(I_C = -2.0 \ mAdc, \ V_{CE} = -5.0 \ V)$	A Series Device B Series Devices C Series Devices BC557 A Series Device B Series Devices	h <sub>FE</sub>	- - 120 120 180	90 150 270 - 170 290	- - 800 220 460	_
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ V})$	C Series Devices A Series Device B Series Devices C Series Devices		420 - - -	500 120 180 300	800 - - -	
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = -0.5 mAdc) (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = see Note 1) (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -5.0 mAdc)		V <sub>CE(sat)</sub>	- - -	-0.075 -0.3 -0.25	-0.3 -0.6 -0.65	V
Base – Emitter Saturation Voltage ( $I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ( $I_C = -100$ mAdc, $I_B = -5.0$ mAdc)		V <sub>BE(sat)</sub>	- -	-0.7 -1.0	<u>-</u>	V
Base–Emitter On Voltage ( $I_C = -2.0$ mAdc, $V_{CE} = -5.0$ Vdc) ( $I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc)		V <sub>BE(on)</sub>	-0.55 -	-0.62 -0.7	-0.7 -0.82	V
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 V, f = 100 MHz)	BC556 BC557 BC558	f <sub>T</sub>	- - -	280 320 360	- - -	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz})$		$C_{ob}$	_	3.0	6.0	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mAdc, V <sub>CE</sub> = $-5.0$ V, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, $\Delta$ f = $200$ Hz)	BC556 BC557 BC558	NF	- - -	2.0 2.0 2.0	10 10 10	dB
Small–Signal Current Gain (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = 5.0 V, f = 1.0 kHz)	BC557 A Series Device B Series Devices C Series Devices	h <sub>fe</sub>	125 125 240 450	- - - -	900 260 500 900	-

<sup>1.</sup>  $I_C = -10$  mAdc on the constant base current characteristics, which yields the point  $I_C = -11$  mAdc,  $V_{CE} = -1.0$  V.

#### BC557/BC558

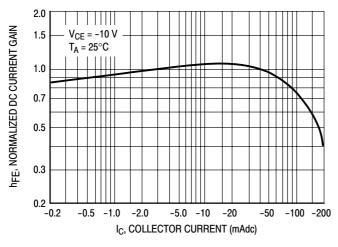


Figure 1. Normalized DC Current Gain

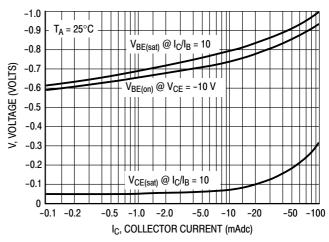


Figure 2. "Saturation" and "On" Voltages

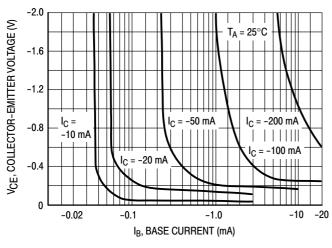


Figure 3. Collector Saturation Region

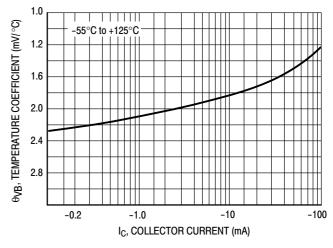


Figure 4. Base-Emitter Temperature Coefficient

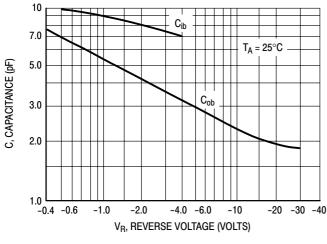


Figure 5. Capacitances

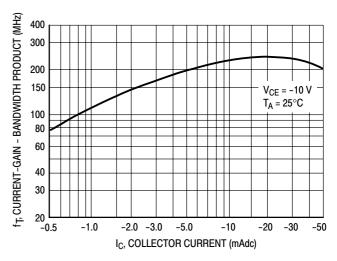


Figure 6. Current-Gain - Bandwidth Product

#### **BC556**

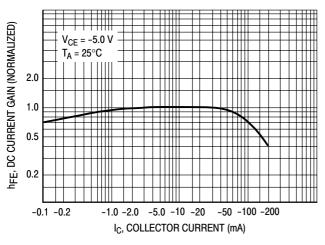


Figure 7. DC Current Gain

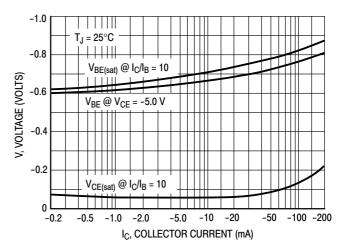


Figure 8. "On" Voltage

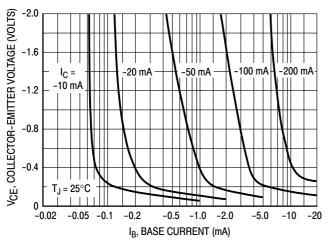


Figure 9. Collector Saturation Region

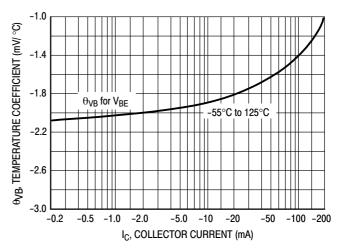


Figure 10. Base-Emitter Temperature Coefficient

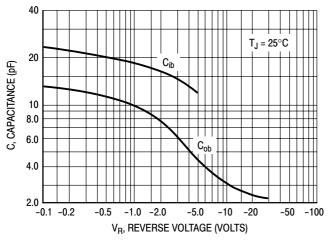


Figure 11. Capacitance

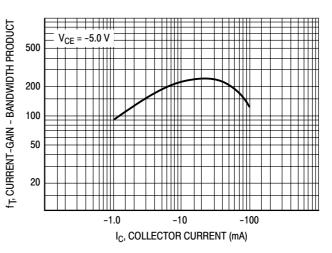


Figure 12. Current-Gain - Bandwidth Product

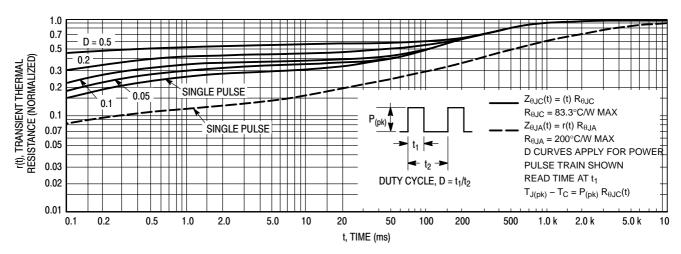


Figure 13. Thermal Response

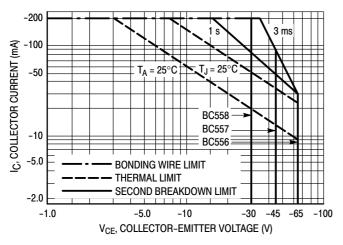


Figure 14. Active Region - Safe Operating Area

The safe operating area curves indicate  $I_C-V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

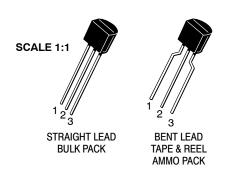
The data of Figure 14 is based upon  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BC556BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC556BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557BRL1	TO-92	2000 / Tape & Reel
BC557BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC557BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC558BRLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

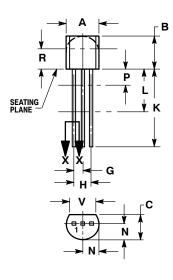
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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**DATE 09 MAR 2007** 

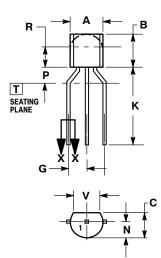


STRAIGHT LEAD **BULK PACK** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R
  IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	.080 0.105 2.04		2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD TAPE & REEL** AMMO PACK



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER

- AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS				
DIM	MIN	MAX			
Α	4.45	5.20			
В	4.32	5.33			
С	3.18	4.19			
D	0.40	0.54			
G	2.40	2.80			
J	0.39	0.50			
K	12.70				
N	2.04	2.66			
P	1.50	4.00			
R	2.93				
٧	3.43				

#### **STYLES ON PAGE 2**

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#### **DATE 09 MAR 2007**

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	
PIN 1. 2.	GATE	PIN 1.	SOURCE	PIN 1.	DRAIN	PIN 1.	BASE 1	2.	CATHODE
2.	ANODE CATHODE & ANODE	2.	GATE	2.	ANODE 1 GATE CATHODE 2	2.	EMITTER COLLECTOR BASE	2.	ANODE 1 CATHODE ANODE 2
2.	ANODE GATE	PIN 1. 2.	COLLECTOR	PIN 1.	ANODE CATHODE NOT CONNECTED	PIN 1.	GATE	PIN 1. 2.	NOT CONNECTED CATHODE ANODE
PIN 1. 2.	COLLECTOR EMITTER	PIN 1.	SOURCE GATE	PIN 1. 2.		PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
	Vcc	PIN 1.	MT SUBSTRATE		CATHODE ANODE	PIN 1. 2.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	DRAIN
PIN 1. 2.	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	PIN 1. 2.	RETURN INPUT OUTPUT	PIN 1. 2.	INPUT		

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